

600V N-Channel MOSFET



TO-220

ITO-220



Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(\Omega)$ (max)	I _D (A)
600	0.75 @ V _{GS} =10V	10

Features

- Advanced high dense cell design.
- High Power and Current handing capability.

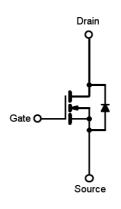
Application

- Power Supply.
- Lighting.

Ordering Information

Part No.	Package	Packing
TSM10N60CZ C0	TO-220	50pcs / Tube
TSM10N60CI C0	ITO-220	50pcs / Tube

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (T_C = 25°C unless otherwise noted)

Parameter		Symbol	Limit		Unit
		Symbol	TO-220	ITO-220	Unit
Drain-Source Voltage		V_{DS}	600		V
Gate-Source Voltage		V_{GS}	±30		V
Continuous Drain Current	$T_C = 25$ °C	l _D ^a	10		A
Continuous Diain Current	T _C = 100 °C		6		
Pulsed Drain Current ^b		I_{DM}^{a}	40		Α
Total Power Dissipation @ T _C =25C		P_{DTOT}	166	50	W
Single Pulsed Avalanche Energy ^c		E_AS	41		mJ
Operating Junction and Storage Temperature Range		T_J,T_STG	- 55 to +150		°C

Thermal Performance

Parameter	Symbol	Limit		Unit
Junction to Case Thermal Resistance	R⊖ _{JC}	0.75	2.5	°C/W
Junction to Ambient Thermal Resistance	$R\Theta_{JA}$	63		°C/W

Notes a: Current limited by package

Notes b: Pulse width limited by the Maximum junction temperature **Notes c:** L=0.75mH, I_{AS} =10A, V_{DD} =50V, R_{G} =25 Ω , Starting T_{i} =25 $^{\circ}$ C



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Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static ^a						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2	3.1	4	V
Gate Body Leakage	$V_{GS} = \pm 30 V, V_{DS} = 0 V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I _{DSS}			20	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 5A$	R _{DS(ON)}		0.61	0.75	Ω
Dynamic ^b						
Total Gate Charge		Q_g		45.8		
Gate-Source Charge	$V_{DS} = 300V, I_{D} = 10A,$	Q_gs		11.5		nC
Gate-Drain Charge	$V_{GS} = 10V$	Q_gd		16		
Input Capacitance		C _{iss}		1738		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C _{oss}		195		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		26.3		
Switching ^b						
Turn-On Delay Time		t _{d(on)}		33.6		
Turn-On Rise Time	$V_{DD} = 300V, R_G = 10\Omega,$	t _r		7.4		
Turn-Off Delay Time	$I_D = 10A$, $V_{GS} = 10V$,	t _{d(off)}		68		nS
Turn-Off Fall Time	1	t _f		15.2		
Source-Drain Diode ^a		•		•	•	
Forward On Voltage	I _S =10A, V _{GS} =0V	VSD		0.8	1.5	V

Notes a: Pulse test: PW ≤300µS, duty cycle ≤2%

Notes b: For DESIGN AID ONLY, not subject to production testing.

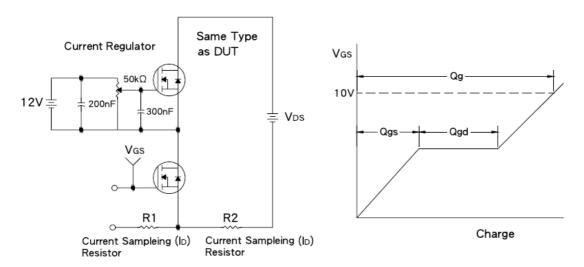
Notes c: Switching time is essentially independent of operating temperature.



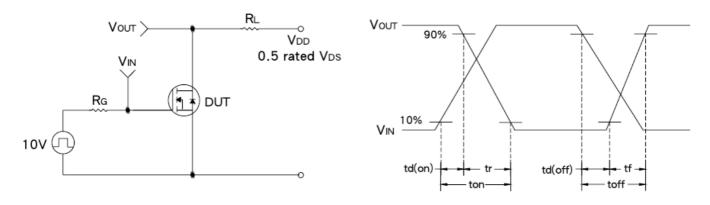
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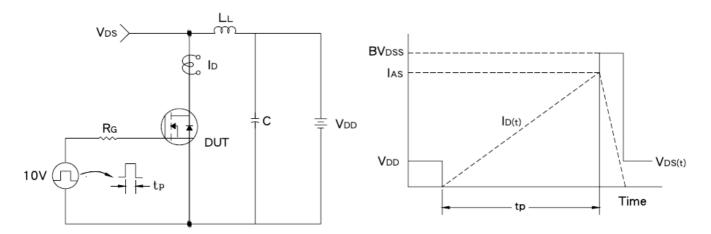
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



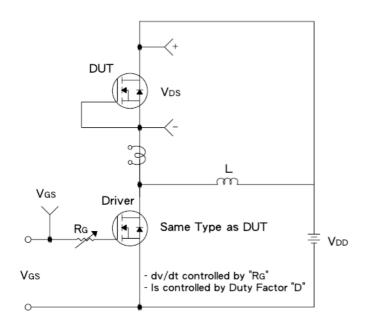
EAS Test Circuit & Waveform



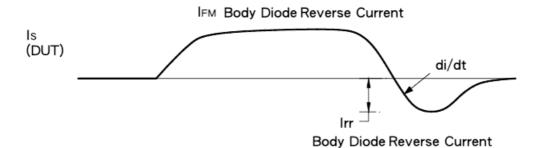
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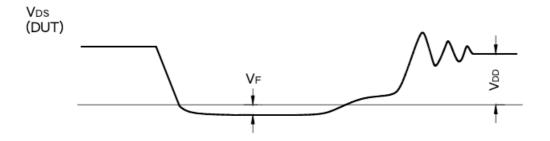


Diode Reverse Recovery Time Test Circuit & Waveform









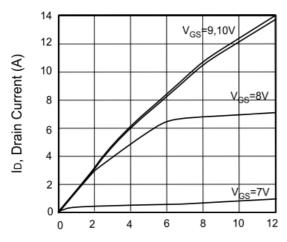


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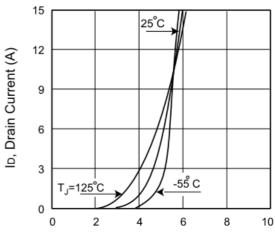
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

Output Characteristics



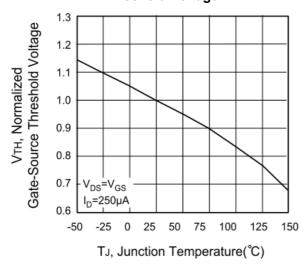
VDS, Drain-to-Source Voltage (V)

Transfer Characteristics

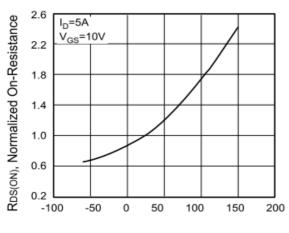


Vgs, Gate-to-Source Voltage (V)

Threshold Voltage

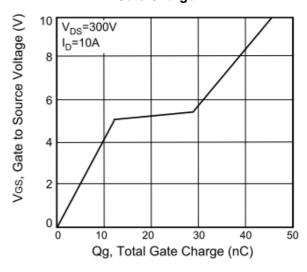


On-Resistance vs. Junction Temperature

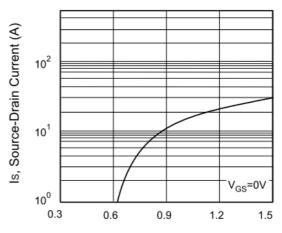


TJ, Junction Temperature(°C)

Gate Charge



Source-Drain Diode Forward Voltage



Vsp, Body Diode Forward Voltage (V)



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C, Capacitance (pF)

0

5

Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

Capacitance Characteristics 3000 2500 2000 1500 C_{iss} C_{oss}

Crss

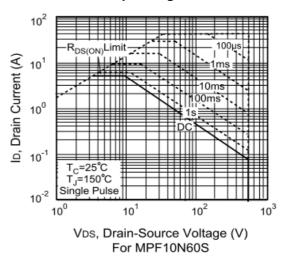
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VDS, Drain-to-Source Voltage (V)

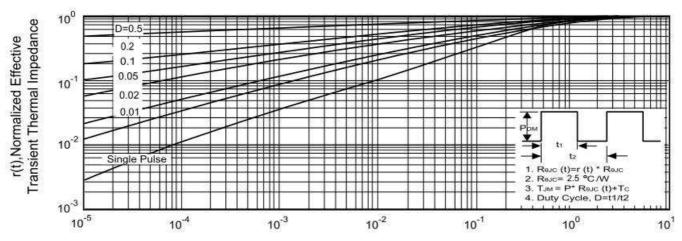
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Maximum Safe Operating Area - ITO-220



Normalized Thermal Transient Impedance, Junction-to-Ambient



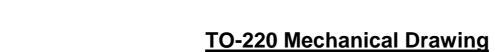
Square Pulse Duration (sec)

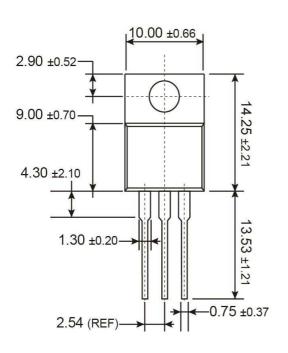
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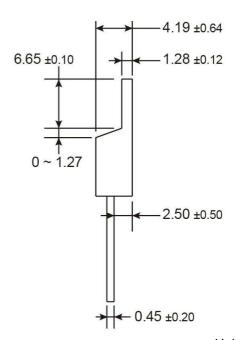
Version: C13



600V N-Channel MOSFET







Unit: Millimeters

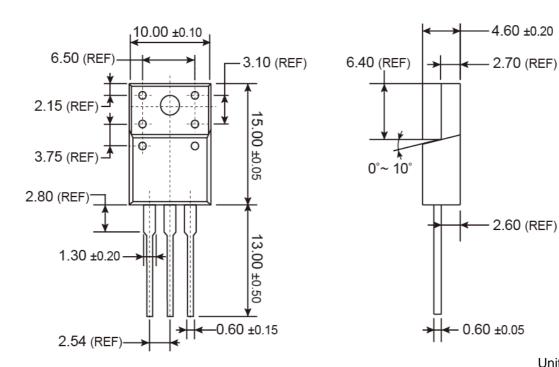
Version: C13

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600V N-Channel MOSFET



ITO-220 Mechanical Drawing



Unit: Millimeters

Version: C13

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